PSMN013-30MLC

N-channel 30 V 13.6 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

Rev. 4 — 15 June 2012 Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching
- Synchronous buck regulator

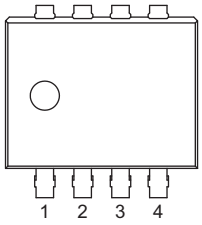
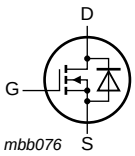
1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C	-	-	30	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1	-	-	39	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2	-	-	38	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 10 A; T_j = 25 °C; see Figure 10	-	14.65	16.9	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; see Figure 10	-	11.8	13.6	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V; see Figure 12; see Figure 13	-	1	-	nC
$Q_{G(tot)}$	total gate charge	V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V; see Figure 12; see Figure 13	-	3.7	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

SOT1210 (LFPAK33)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN013-30MLC	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see Figure 1	-	39	A
		V_{GS} = 10 V; T_{mb} = 100 °C; see Figure 1	-	28	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C; see Figure 4	-	157	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2	-	38	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	100	-	V
Source-drain diode					
I_S	source current	T_{mb} = 25 °C	-	34	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C	-	157	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 39 A; $V_{sup} \leq 30$ V; R_{GS} = 50 Ω; unclamped; see Figure 3	-	5.6	mJ

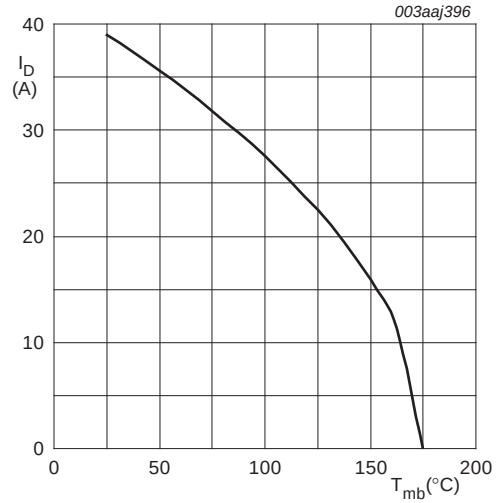


Fig 1. Continuous drain current as a function of mounting base temperature

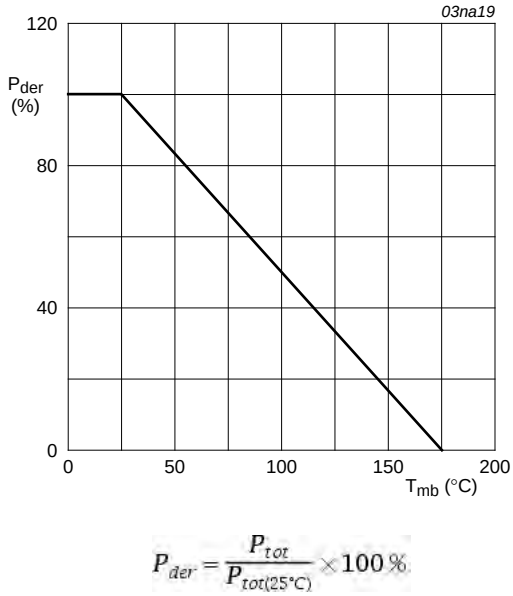


Fig 2. Normalized total power dissipation as a function of mounting base temperature

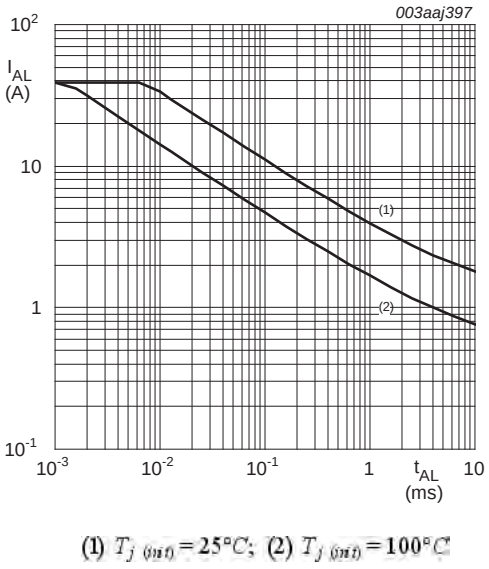


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

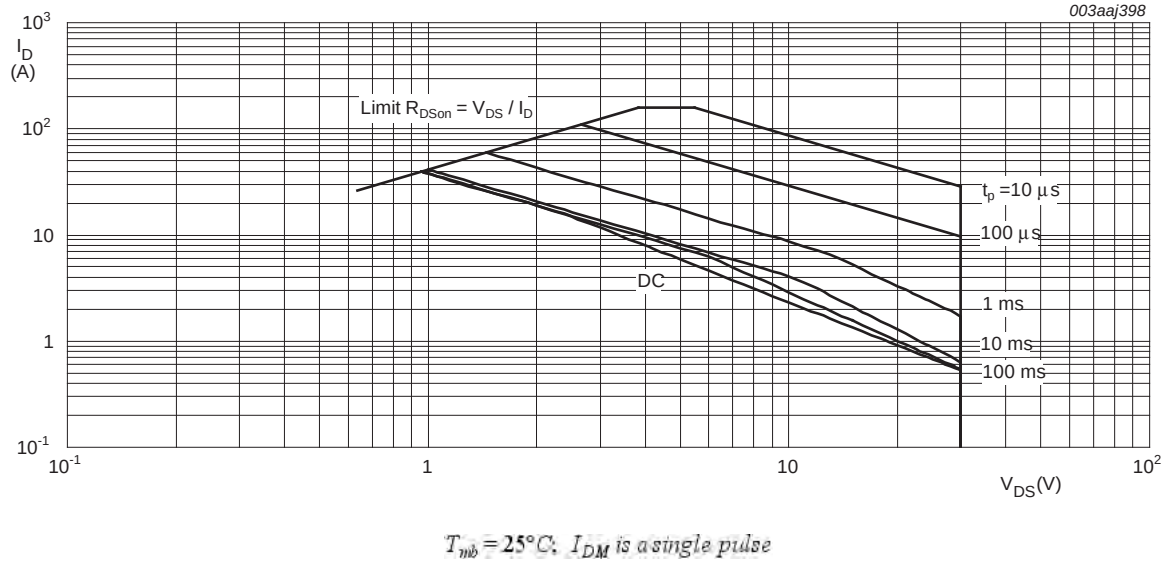


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	3.8	3.99	K/W

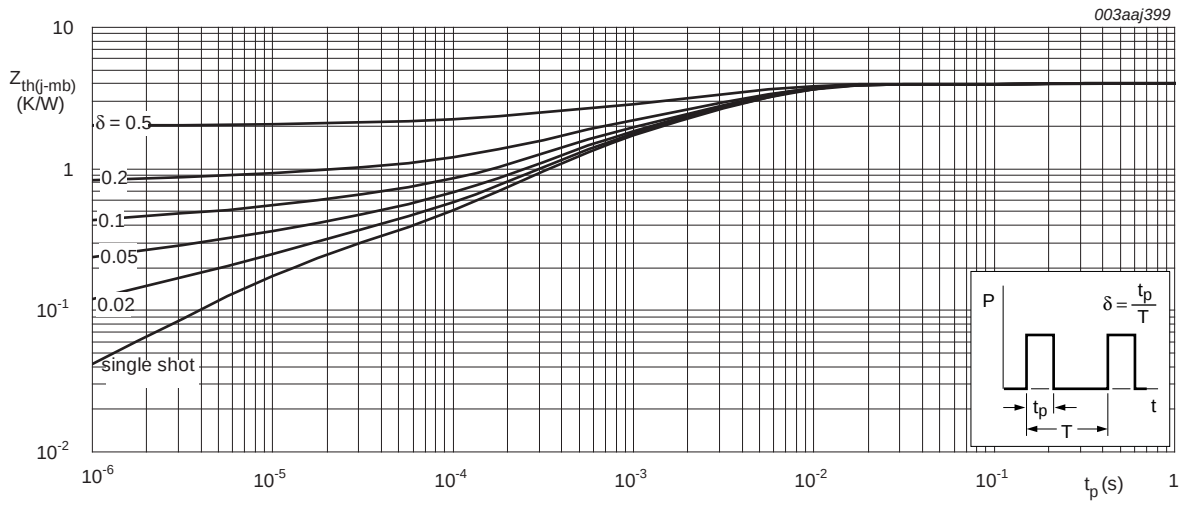


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C	1.3	1.66	1.95	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature		-	-4	-	mV/K
I_{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	µA
		V_{DS} = 30 V; V_{GS} = 0 V; T_j = 150 °C	-	-	100	µA
I_{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 10 A; T_j = 25 °C; see Figure 10	-	14.65	16.9	mΩ
		V_{GS} = 4.5 V; I_D = 10 A; T_j = 150 °C; see Figure 10; see Figure 11	-	-	28.75	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; see Figure 10	-	11.8	13.6	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 150 °C; see Figure 11; see Figure 10	-	-	22.95	mΩ
R_G	gate resistance	f = 1 MHz	0.85	1.7	3.4	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 10 A; V_{DS} = 15 V; V_{GS} = 10 V; see Figure 12; see Figure 13	-	8	-	nC
		I_D = 10 A; V_{DS} = 15 V; V_{GS} = 4.5 V; see Figure 12; see Figure 13	-	3.7	-	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V	-	7.4	-	nC
Q_{GS}	gate-source charge	I_D = 10 A; V_{DS} = 15 V; V_{GS} = 4.5 V; see Figure 12; see Figure 13	-	1.2	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	0.8	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	0.4	-	nC
Q_{GD}	gate-drain charge		-	1	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 10 A; V_{DS} = 15 V; see Figure 12; see Figure 13	-	2.6	-	V
C_{iss}	input capacitance	V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 14	-	519	-	pF
C_{oss}	output capacitance		-	131	-	pF
C_{rss}	reverse transfer capacitance		-	37	-	pF

Table 6. Characteristics *…continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; R_L = 1.5 Ω; V_{GS} = 4.5 V; $R_{G(ext)}$ = 5 Ω	-	7	-	ns
t_r	rise time		-	9.8	-	ns
$t_{d(off)}$	turn-off delay time		-	9.6	-	ns
t_f	fall time		-	5.5	-	ns
Q_{oss}	output charge	V_{GS} = 0 V; V_{DS} = 15 V; f = 1 MHz; T_j = 25 °C	-	3.7	-	nC
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 10 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 15	-	0.86	1.1	V
t_{rr}	reverse recovery time	I_S = 10 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 15 V	-	13.4	-	ns
Q_r	recovered charge		-	6.6	-	nC
t_a	reverse recovery rise time	V_{GS} = 0 V; I_S = 10 A; dI_S/dt = -100 A/µs; V_{DS} = 15 V; see Figure 16	-	8.6	-	ns
t_b	reverse recovery fall time		-	4.8	-	ns

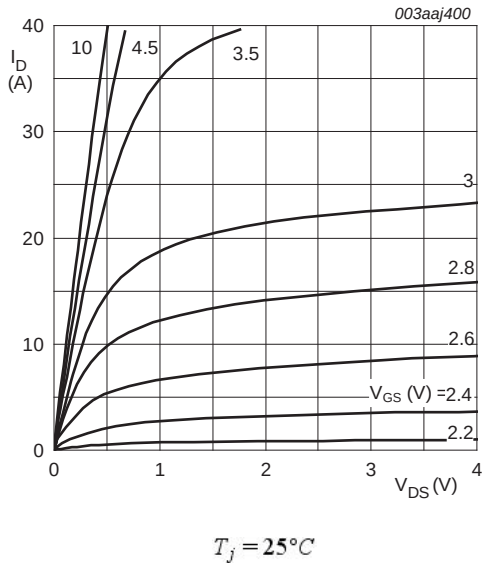


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

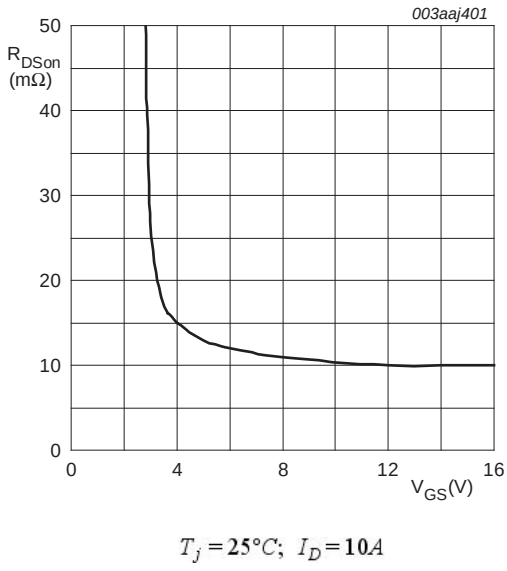
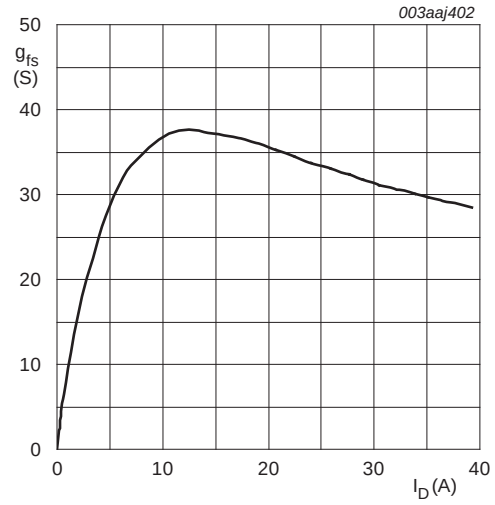
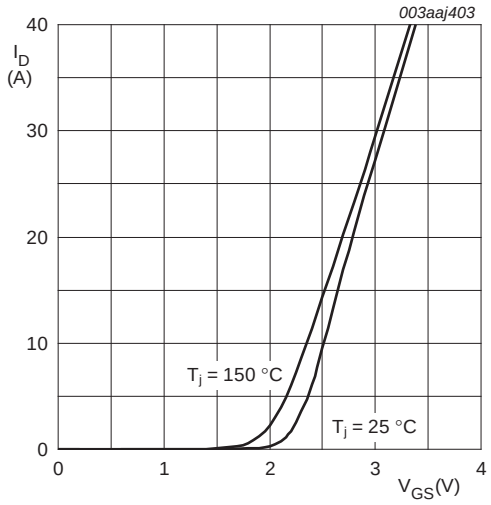


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



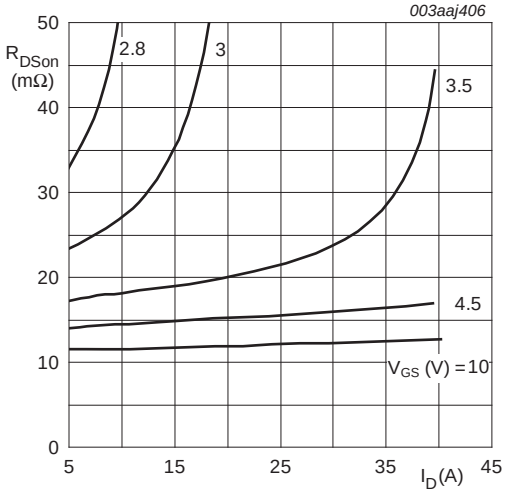
$T_j = 25°C;\ V_{DS} = 10V$

Fig 8. Forward transconductance as a function of drain current; typical values



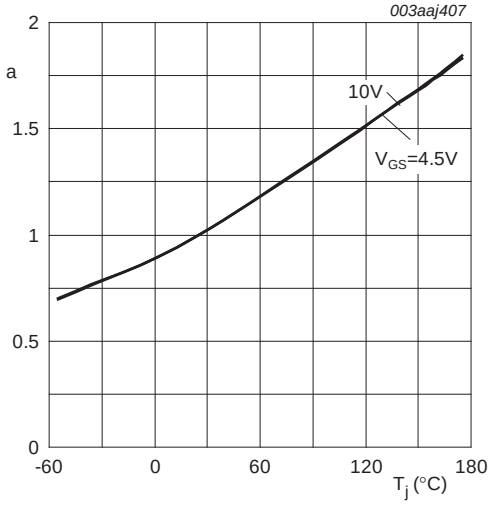
$V_{DS} = 10V$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



$T_j = 25°C$

Fig 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

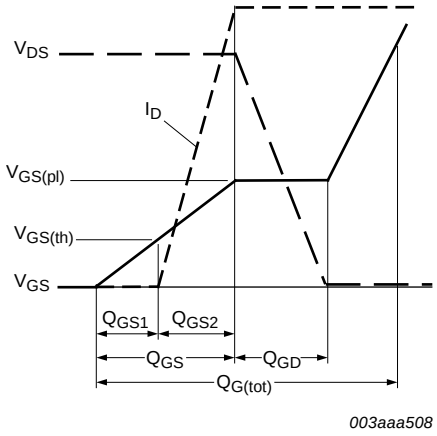
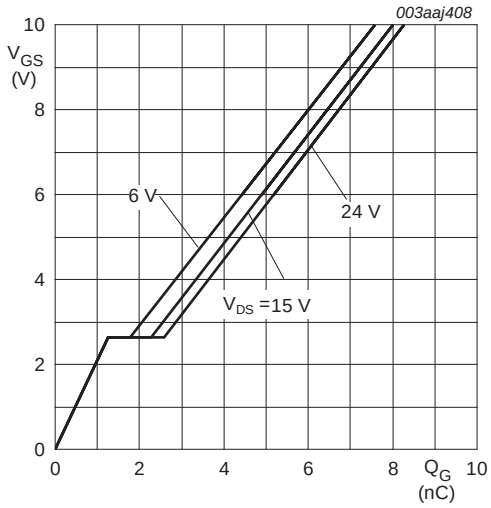
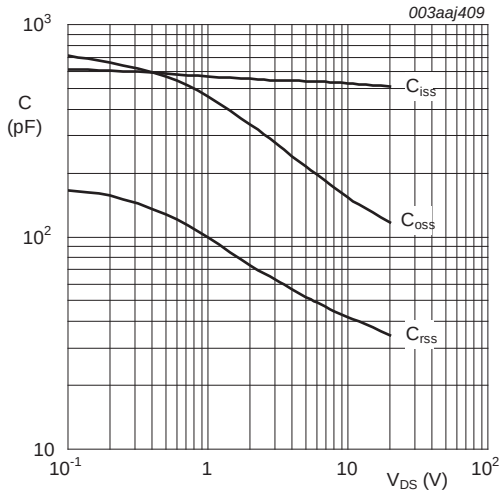


Fig 12. Gate charge waveform definitions



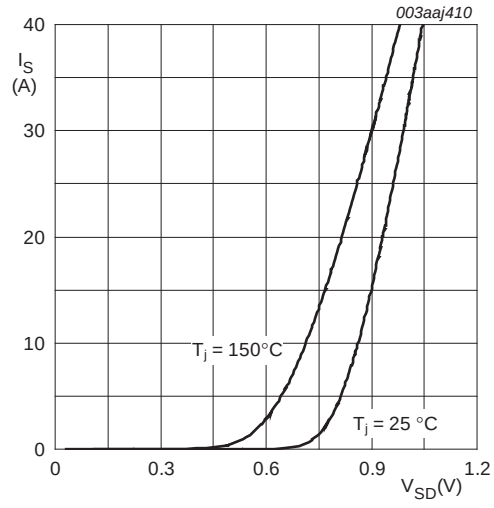
$T_j = 25°C;\ I_D = 10A$

Fig 13. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V;\ f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0V$

Fig 15. Source current as a function of source-drain voltage; typical values

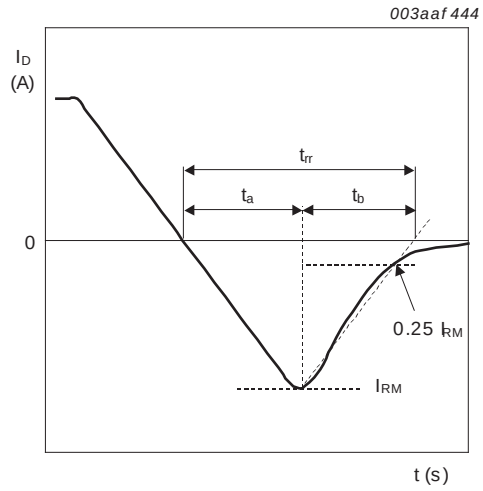
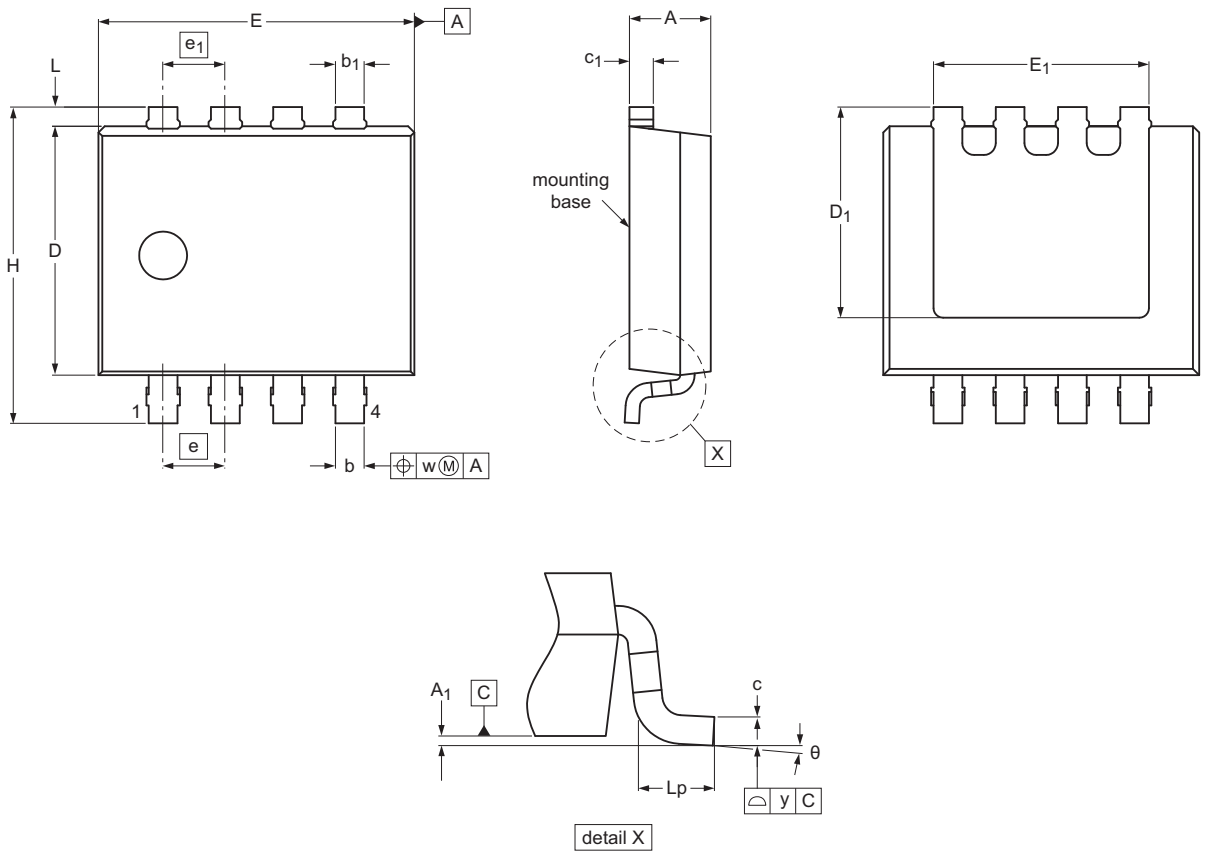


Fig 16. Reverse recovery timing definition

7. Package outline

Plastic single ended surface mounted package (LFPAK33); 8 leads **SOT1210**



0 2.5 5 mm

scale

Dimensions

Unit(1)		A	A_1	b	b_1	c	c_1	D(1)	D_1	E(1)	E_1	e	e_1	H	L	L_p	w	y	θ
mm	max	0.90	0.10	0.35	0.35	0.20	0.30	2.70	2.35	3.40	2.45			3.40	0.25	0.50			8°
	nom											0.65	0.65				0.20	0.10	
	min	0.80	0.00	0.25	0.25	0.10	0.20	2.50	1.90	3.20	2.00			3.20	0.13	0.30			0°

Note
1. Plastic or metal protrusions of 0.15 mm per side are not included.

sot1210_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1210						~~11-12-19~~ 12-03-12

Fig 17. Package outline SOT1210 (LFPAK33)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN013-30MLC v.4	20120615	Product data sheet	-	PSMN013-30MLC v.3
Modifications:	• Status changed from objective to product. • Various changes to content.			
PSMN013-30MLC v.3	20120607	Objective data sheet	-	PSMN013-30MLC v.2

9. Legal information

9.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URLhttp://www.nxp.com.

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11. Contents

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Date of release: 15 June 2012
Document identifier: PSMN013-30MLC